

2-Line ESD protection

Discription

The FTV05CA883 is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

Applications

- · Cellular phones audio
- MP3 players
- Digital cameras
- Portable applicationss
- mobile telephone

Features

- Small Body Outline Dimensions: 0.039" x 0.024(1.0 mm x 0.60 mm)
- Low Body Height: 0.020" (0.50 mm)
- Protects two data lines
- Working voltage: 5V
- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- These are Pb-Free Devices
- We declare that the material of product compliance with RoHS requirements.

MAXIMUM RATINGS

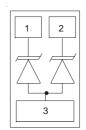
Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Air discharge Contact discharge		± 20 ± 16	kV kV
ESD Voltage Per Human Body Model		16	kV
Total Power Dissipation on FR-5 Board (Note 1) @ $T_A=25$	PD	250	mW
Junction and Storage Temperature Range	TJ,TSTG	-55 to 150	
Lead Solder Temperature – Maximum (10 Second Duration)	TL	260	

Stresses exceeding Maximum Ratings may damage the device. Maximum Rating are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = 1.0*0.75*0.62 in.







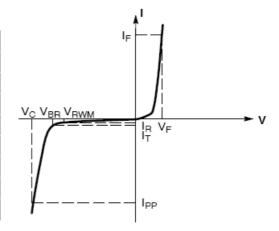
Ordering information

Device	Marking	Shipping		
FTV05CA883	68	10000/Tape&Reel		



Electrical Parameter

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V_{RWM}
Ι _Τ	Test Current
V _{BR}	Breakdown Voltage @ I _T
I _F	Forward Current
V _F	Forward Voltage @ I _F



Uni-Directional TVS

	V _{RWM}	la.	V _{BR}	Ι _Τ	Inn	Vc	Р _{РК}	С
Device					I _{PP}			
	(V)	(! A)	(V)	″mA#	(A)	(V)	(W)	(pF)
		@	@ I _T			@ Max I _{PP}	(8*20 µs)	
		V_{RWM}	(Note 2)		(Note 3)	(Note 3)		
	Max	Max	Min		Max	Max	Тур	Тур
FTV05CA883	5.0	1.0	6.0	1.0	7	11.0	77	40

Other voltage available upon request.

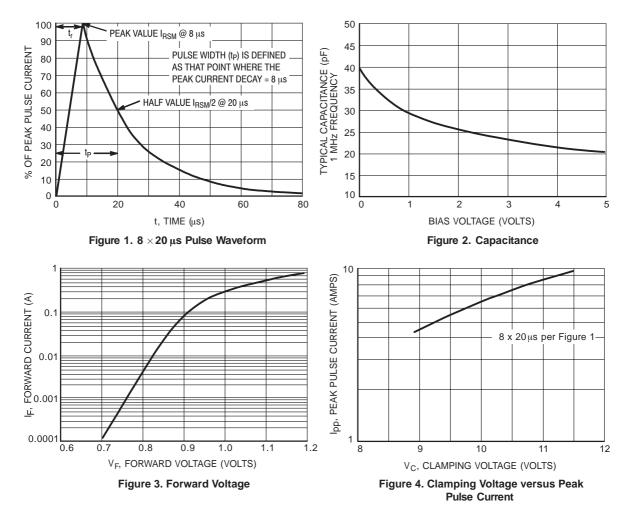
2. V_{BR} is measured with a pulse test current IT at an ambient temperature of 25 $^\circ\!\!\!\mathrm{C}$

3. Surge current waveform per Figure 1.



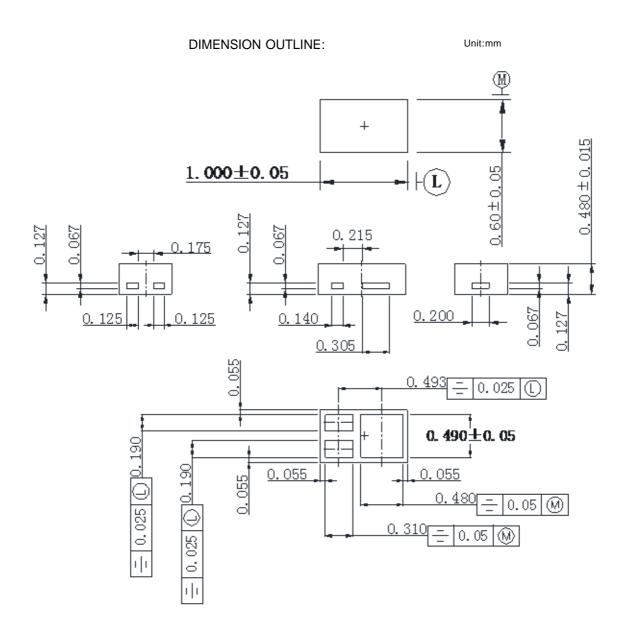
FTV05CA883

TYPICAL CHARACTERISTICS





SOT-883



First Silicon